

MBT3946DW1T1

Dual General Purpose Transistor

The MBT3946DW1T1 device is a spin-off of our popular SOT-23/SOT-323 three-leaded device. It is designed for general purpose amplifier applications and is housed in the SOT-363-6 surface mount package. By putting two discrete devices in one package, this device is ideal for low-power surface mount applications where board space is at a premium.

- h_{FE} , 100–300
- Low $V_{CE(sat)}$, ≤ 0.4 V
- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- Available in 8 mm, 7-inch/3,000 Unit Tape and Reel
- Device Marking: MBT3946DW1T1 = 46
- Pb-Free Package May be Available. The G-Suffix Denotes a Pb-Free Lead Finish

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage (NPN) (PNP)	V_{CEO}	40 –40	Vdc
Collector – Base Voltage (NPN) (PNP)	V_{CBO}	60 –40	Vdc
Emitter – Base Voltage (NPN) (PNP)	V_{EBO}	6.0 –5.0	Vdc
Collector Current – Continuous (NPN) (PNP)	I_C	200 –200	mAdc
Electrostatic Discharge	ESD	HBM>16000, MM>2000	V

THERMAL CHARACTERISTICS

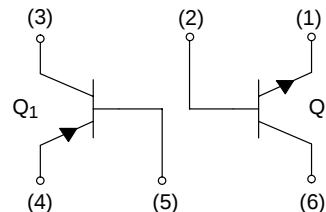
Characteristic	Symbol	Max	Unit
Total Package Dissipation (Note 1) $T_A = 25^\circ\text{C}$	P_D	150	mW
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	833	$^\circ\text{C/W}$
Junction and Storage Temperature Range	T_J, T_{stg}	–55 to +150	$^\circ\text{C}$

1. Device mounted on FR4 glass epoxy printed circuit board using the minimum recommended footprint.



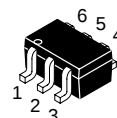
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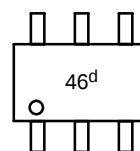
MBT3946DW1T1*

*Q1 PNP
Q2 NPN



**SOT-363-6/SC-88
CASE 419B
Style 1**

MARKING DIAGRAM



46 = Specific Device Code
d = Date Code

ORDERING INFORMATION

Device	Package	Shipping†
MBT3946DW1T1	SOT-363	3000/Tape & Reel
MBT3946DW1T1G	SOT-363	3000/Tape & Reel
MBT3946DW1T2	SOT-363	3000/Tape & Reel
MBT3946DW1T2G	SOT-363	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MBT3946DW1T1

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage (Note 2) (I _C = 1.0 mA _{dc} , I _B = 0) (NPN) (I _C = –1.0 mA _{dc} , I _B = 0) (PNP)	V _{(BR)CEO}	40 –40	– –	V _{dc}
Collector–Base Breakdown Voltage (I _C = 10 μA _{dc} , I _E = 0) (NPN) (I _C = –10 μA _{dc} , I _E = 0) (PNP)	V _{(BR)CBO}	60 –40	– –	V _{dc}
Emitter–Base Breakdown Voltage (I _E = 10 μA _{dc} , I _C = 0) (NPN) (I _E = –10 μA _{dc} , I _C = 0) (PNP)	V _{(BR)EBO}	6.0 –5.0	– –	V _{dc}
Base Cutoff Current (V _{CE} = 30 V _{dc} , V _{EB} = 3.0 V _{dc}) (NPN) (V _{CE} = –30 V _{dc} , V _{EB} = –3.0 V _{dc}) (PNP)	I _{BL}	– –	50 –50	nA _{dc}
Collector Cutoff Current (V _{CE} = 30 V _{dc} , V _{EB} = 3.0 V _{dc}) (NPN) (V _{CE} = –30 V _{dc} , V _{EB} = –3.0 V _{dc}) (PNP)	I _{CEX}	– –	50 –50	nA _{dc}
ON CHARACTERISTICS (Note 2)				
DC Current Gain (I _C = 0.1 mA _{dc} , V _{CE} = 1.0 V _{dc}) (NPN) (I _C = 1.0 mA _{dc} , V _{CE} = 1.0 V _{dc}) (I _C = 10 mA _{dc} , V _{CE} = 1.0 V _{dc}) (I _C = 50 mA _{dc} , V _{CE} = 1.0 V _{dc}) (I _C = 100 mA _{dc} , V _{CE} = 1.0 V _{dc}) (I _C = –0.1 mA _{dc} , V _{CE} = –1.0 V _{dc}) (PNP) (I _C = –1.0 mA _{dc} , V _{CE} = –1.0 V _{dc}) (I _C = –10 mA _{dc} , V _{CE} = –1.0 V _{dc}) (I _C = –50 mA _{dc} , V _{CE} = –1.0 V _{dc}) (I _C = –100 mA _{dc} , V _{CE} = –1.0 V _{dc})	h _{FE}	40 70 100 60 30 60 80 100 60 30	– – 300 – – – – 300 – –	–
Collector–Emitter Saturation Voltage (I _C = 10 mA _{dc} , I _B = 1.0 mA _{dc}) (NPN) (I _C = 50 mA _{dc} , I _B = 5.0 mA _{dc}) (I _C = –10 mA _{dc} , I _B = –1.0 mA _{dc}) (PNP) (I _C = –50 mA _{dc} , I _B = –5.0 mA _{dc})	V _{CE(sat)}	– – – –	0.2 0.3 –0.25 –0.4	V _{dc}
Base–Emitter Saturation Voltage (I _C = 10 mA _{dc} , I _B = 1.0 mA _{dc}) (NPN) (I _C = 50 mA _{dc} , I _B = 5.0 mA _{dc}) (I _C = –10 mA _{dc} , I _B = –1.0 mA _{dc}) (PNP) (I _C = –50 mA _{dc} , I _B = –5.0 mA _{dc})	V _{BE(sat)}	0.65 – –0.65 –	0.85 0.95 –0.85 –0.95	V _{dc}
SMALL–SIGNAL CHARACTERISTICS				
Current–Gain – Bandwidth Product (I _C = 10 mA _{dc} , V _{CE} = 20 V _{dc} , f = 100 MHz) (NPN) (I _C = –10 mA _{dc} , V _{CE} = –20 V _{dc} , f = 100 MHz) (PNP)	f _T	300 250	– –	MHz
Output Capacitance (V _{CB} = 5.0 V _{dc} , I _E = 0, f = 1.0 MHz) (NPN) (V _{CB} = –5.0 V _{dc} , I _E = 0, f = 1.0 MHz) (PNP)	C _{obo}	– –	4.0 4.5	pF
Input Capacitance (V _{EB} = 0.5 V _{dc} , I _C = 0, f = 1.0 MHz) (NPN) (V _{EB} = –0.5 V _{dc} , I _C = 0, f = 1.0 MHz) (PNP)	C _{ibo}	– –	8.0 10.0	pF

2. Pulse Test: Pulse Width ≤ 300 μs; Duty Cycle ≤ 2.0%.

MBT3946DW1T1

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
Input Impedance (V _{CE} = 10 Vdc, I _C = 1.0 mA, f = 1.0 kHz) (NPN) (V _{CE} = -10 Vdc, I _C = -1.0 mA, f = 1.0 kHz) (PNP)	h _{ie}	1.0 2.0	10 12	kΩ
Voltage Feedback Ratio (V _{CE} = 10 Vdc, I _C = 1.0 mA, f = 1.0 kHz) (NPN) (V _{CE} = -10 Vdc, I _C = -1.0 mA, f = 1.0 kHz) (PNP)	h _{re}	0.5 0.1	8.0 10	X 10 ⁻⁴
Small-Signal Current Gain (V _{CE} = 10 Vdc, I _C = 1.0 mA, f = 1.0 kHz) (NPN) (V _{CE} = -10 Vdc, I _C = -1.0 mA, f = 1.0 kHz) (PNP)	h _{fe}	100 100	400 400	—
Output Admittance (V _{CE} = 10 Vdc, I _C = 1.0 mA, f = 1.0 kHz) (NPN) (V _{CE} = -10 Vdc, I _C = -1.0 mA, f = 1.0 kHz) (PNP)	h _{oe}	1.0 3.0	40 60	μmhos
Noise Figure (V _{CE} = 5.0 Vdc, I _C = 100 μA, R _S = 1.0 kΩ, f = 1.0 kHz) (NPN) (V _{CE} = -5.0 Vdc, I _C = -100 μA, R _S = 1.0 kΩ, f = 1.0 kHz) (PNP)	NF	— —	5.0 4.0	dB

SWITCHING CHARACTERISTICS

Delay Time	(V _{CC} = 3.0 Vdc, V _{BE} = -0.5 Vdc) (NPN) (V _{CC} = -3.0 Vdc, V _{BE} = 0.5 Vdc) (PNP)	t _d	— —	35 35	ns
Rise Time	(I _C = 10 mA, I _{B1} = 1.0 mA) (NPN) (I _C = -10 mA, I _{B1} = -1.0 mA) (PNP)	t _r	— —	35 35	
Storage Time	(V _{CC} = 3.0 Vdc, I _C = 10 mA) (NPN) (V _{CC} = -3.0 Vdc, I _C = -10 mA) (PNP)	t _s	— —	200 225	ns
Fall Time	(I _{B1} = I _{B2} = 1.0 mA) (NPN) (I _{B1} = I _{B2} = -1.0 mA) (PNP)	t _f	— —	50 75	

MBT3946DW1T1

(NPN)

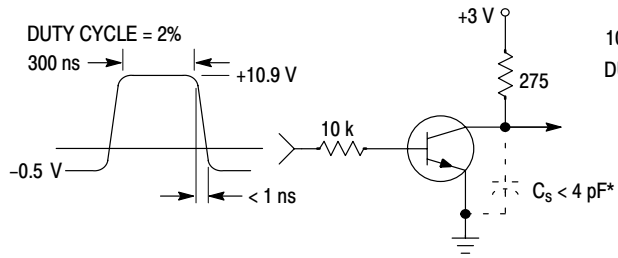


Figure 1. Delay and Rise Time
Equivalent Test Circuit

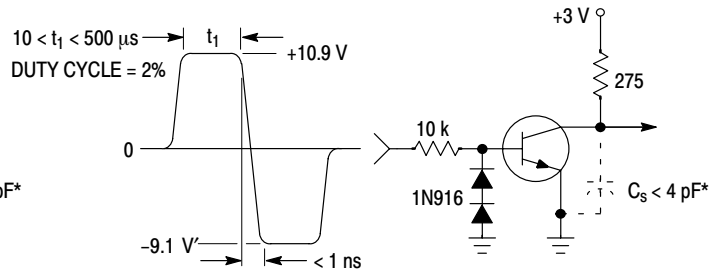


Figure 2. Storage and Fall Time
Equivalent Test Circuit

* Total shunt capacitance of test jig and connectors

TYPICAL TRANSIENT CHARACTERISTICS

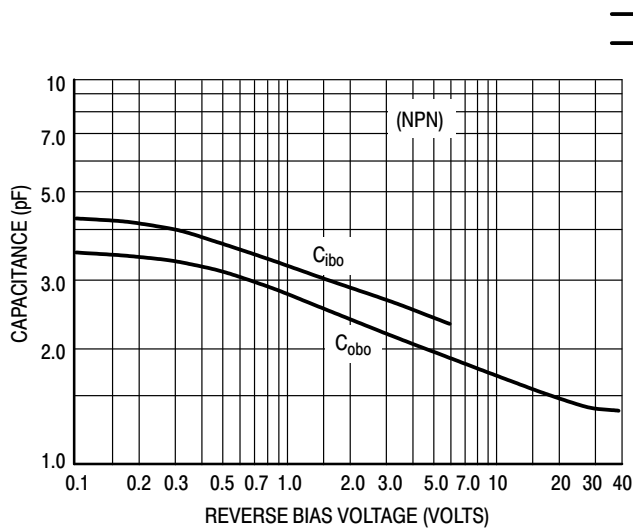


Figure 3. Capacitance

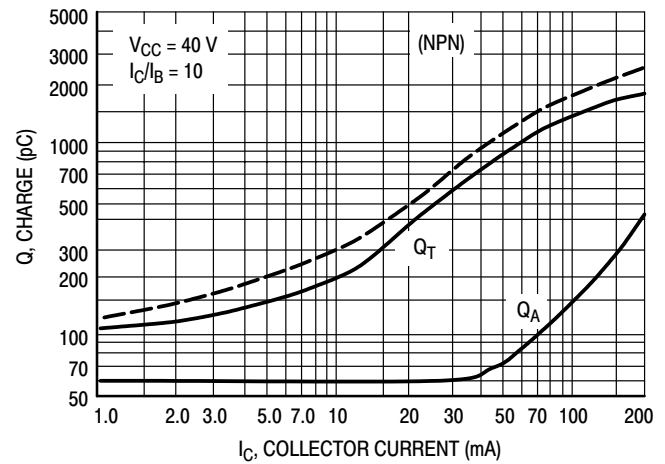


Figure 4. Charge Data

MBT3946DW1T1

(NPN)

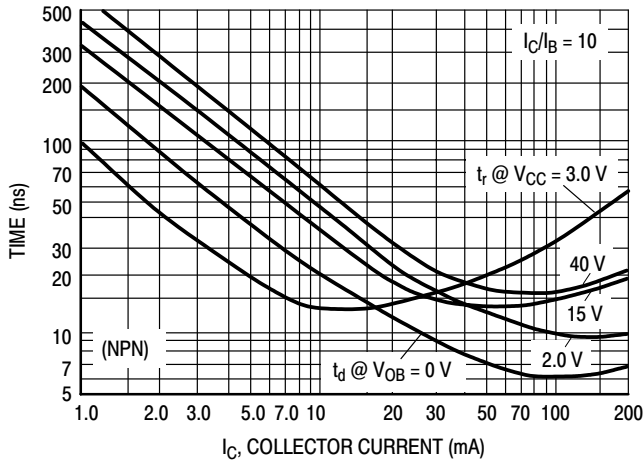


Figure 5. Turn-On Time

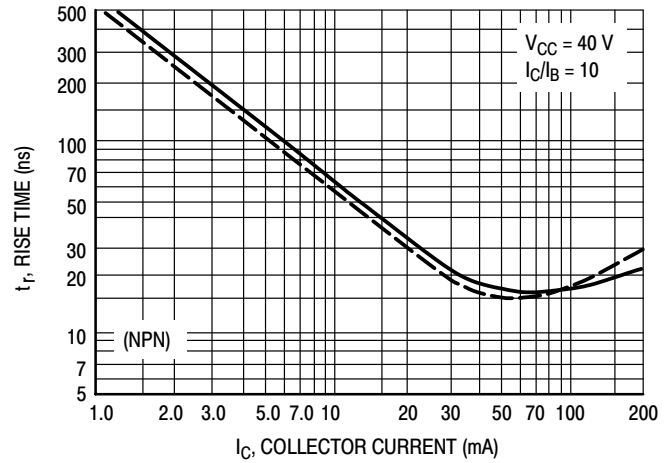


Figure 6. Rise Time

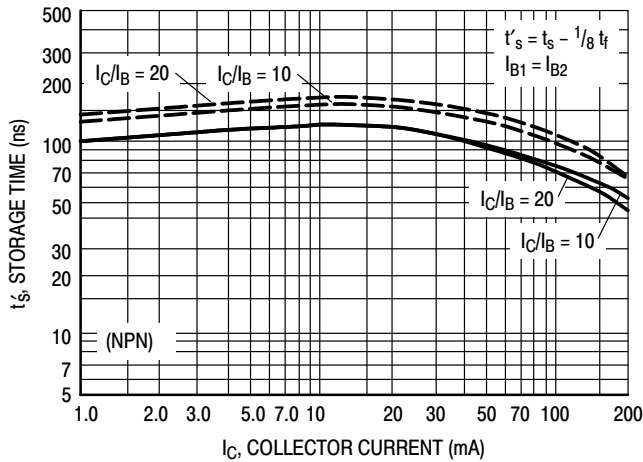


Figure 7. Storage Time

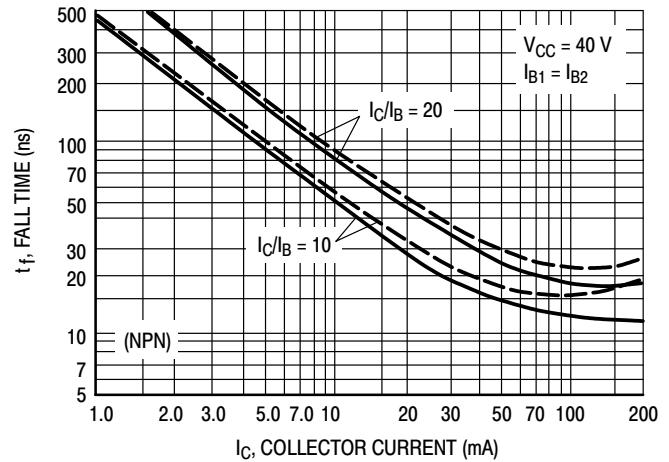


Figure 8. Fall Time

TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

($V_{CE} = 5.0$ Vdc, $T_A = 25^\circ\text{C}$, Bandwidth = 1.0 Hz)

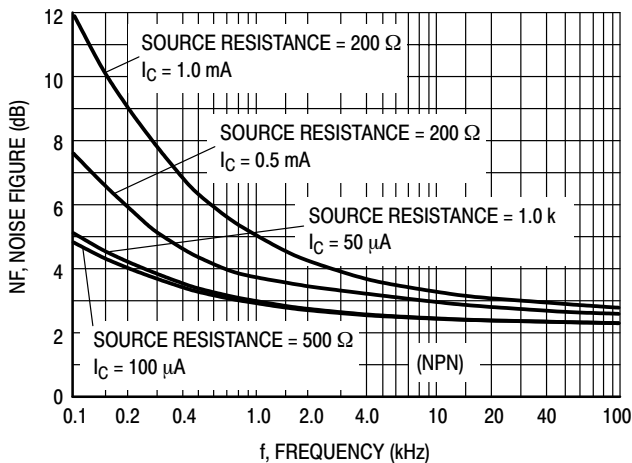


Figure 9. Noise Figure

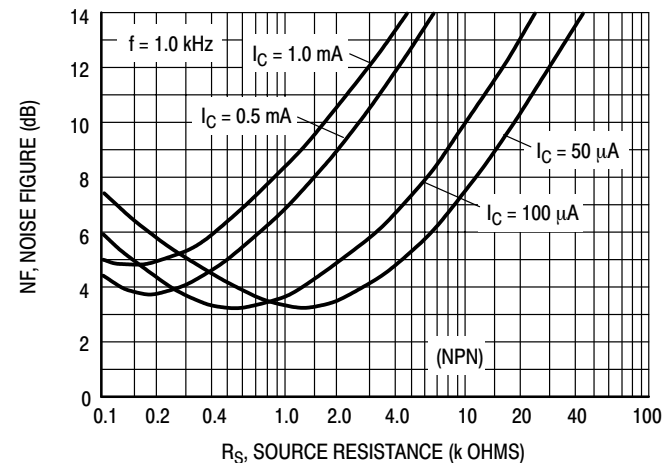


Figure 10. Noise Figure

MBT3946DW1T1

(NPN)

h PARAMETERS

($V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$, $T_A = 25^\circ\text{C}$)

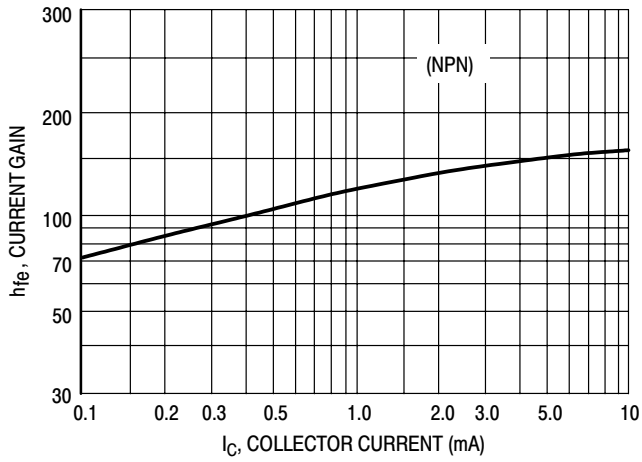


Figure 11. Current Gain

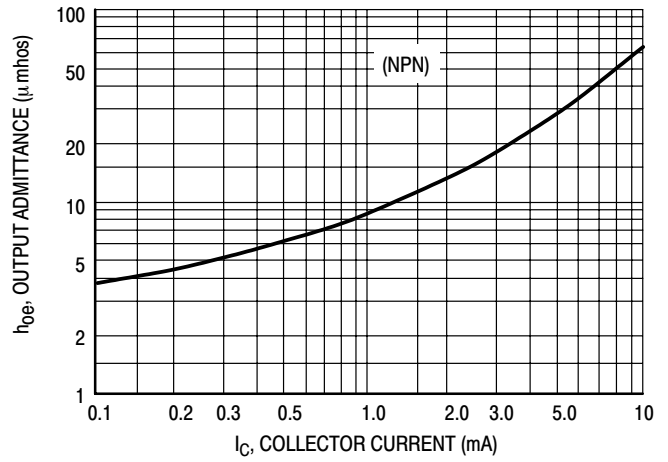


Figure 12. Output Admittance

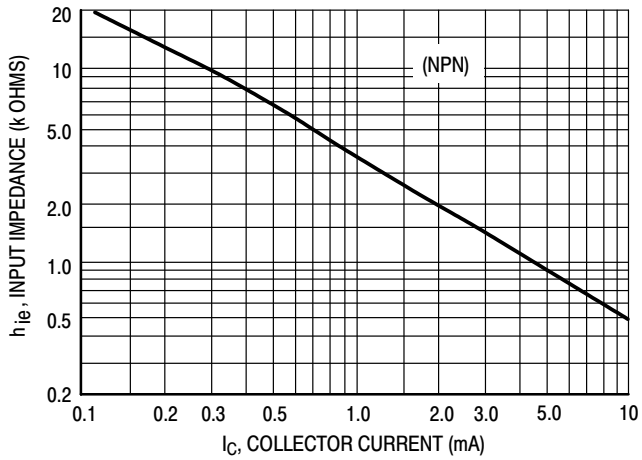


Figure 13. Input Impedance

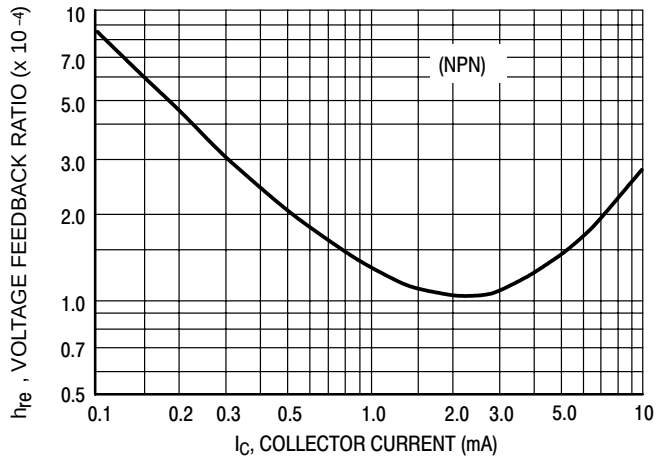


Figure 14. Voltage Feedback Ratio

MBT3946DW1T1

(NPN) TYPICAL STATIC CHARACTERISTICS

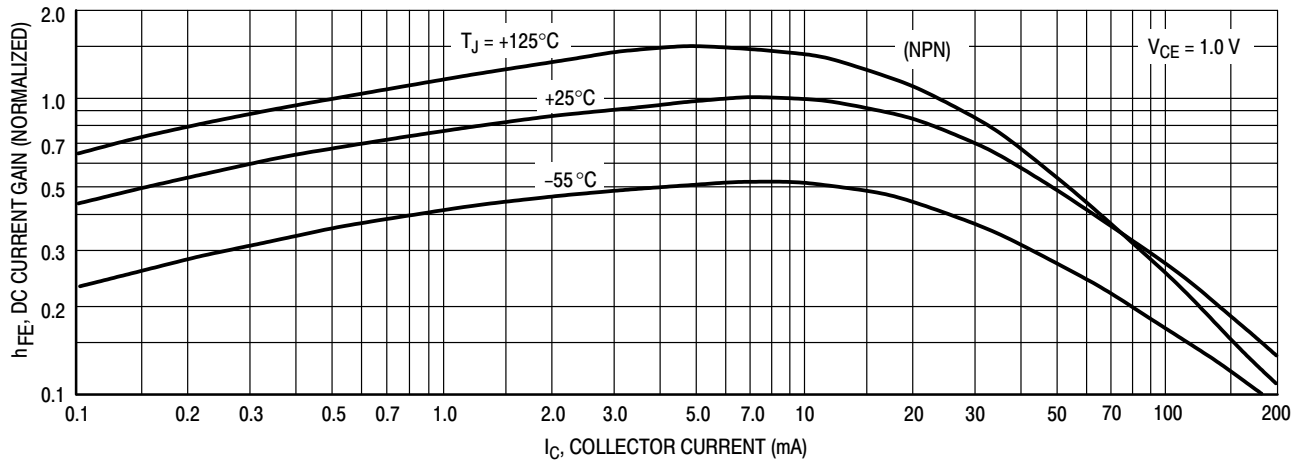


Figure 15. DC Current Gain

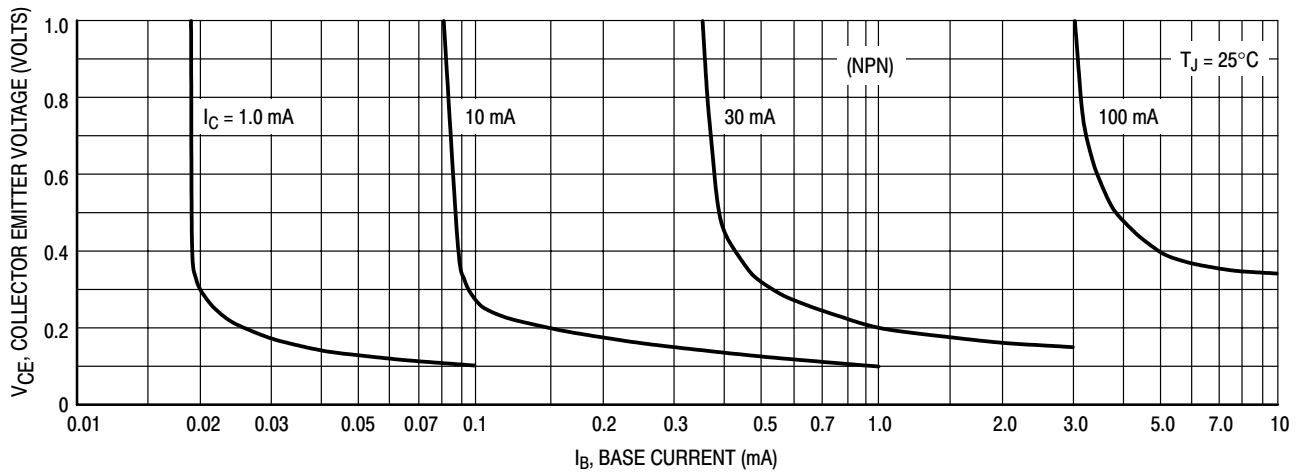


Figure 16. Collector Saturation Region

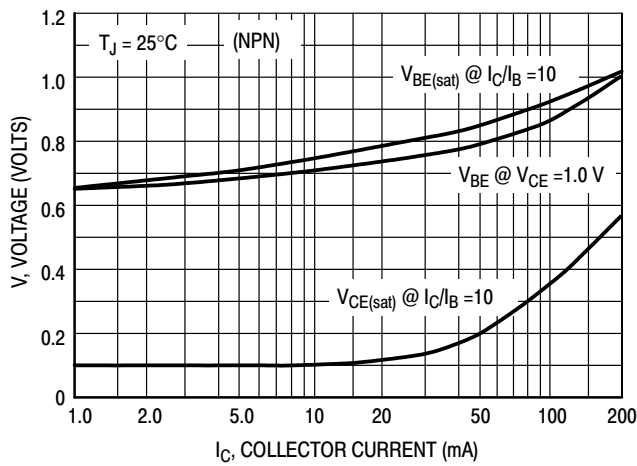


Figure 17. "ON" Voltages

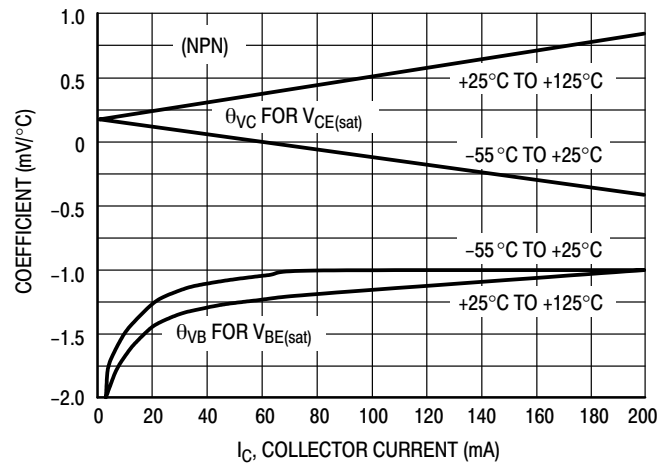


Figure 18. Temperature Coefficients

MBT3946DW1T1

(PNP)

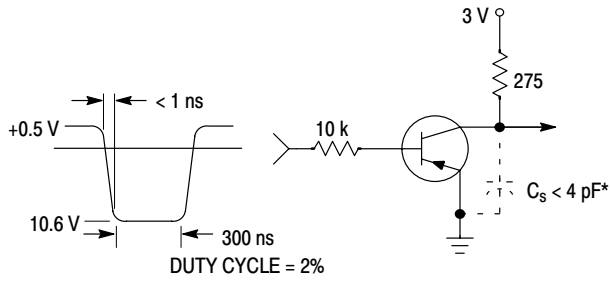


Figure 19. Delay and Rise Time Equivalent Test Circuit

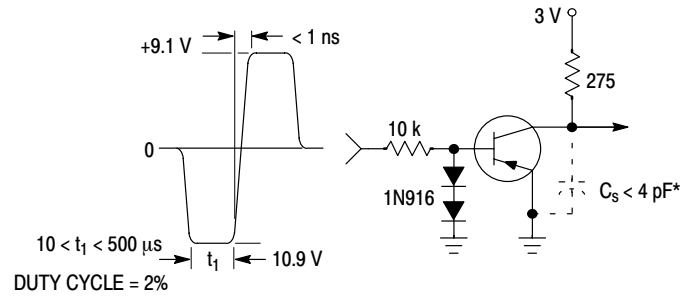


Figure 20. Storage and Fall Time Equivalent Test Circuit

* Total shunt capacitance of test jig and connectors

TYPICAL TRANSIENT CHARACTERISTICS

— $T_J = 25^\circ\text{C}$
 - - $T_J = 125^\circ\text{C}$

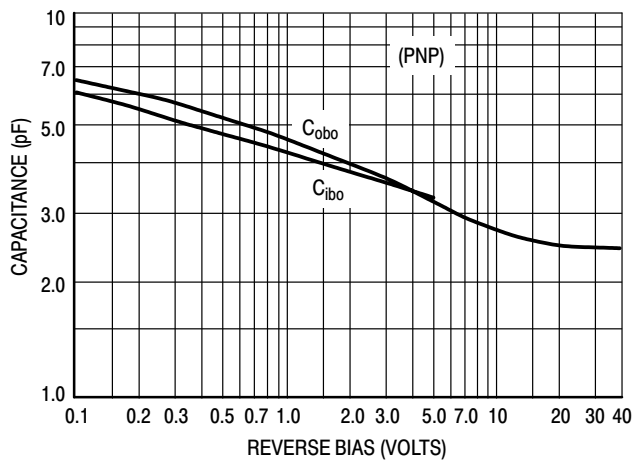


Figure 21. Capacitance

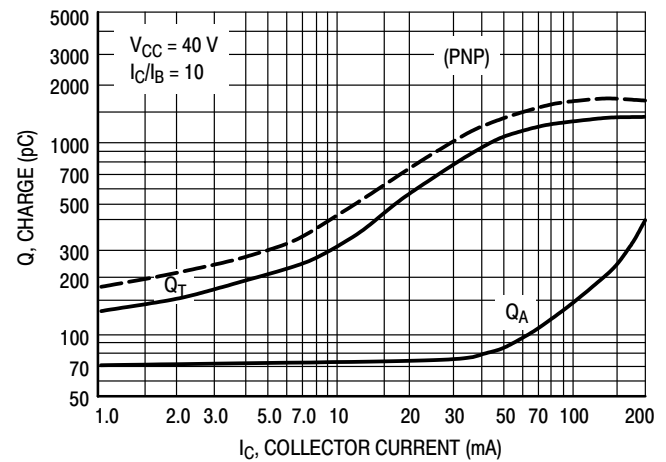


Figure 22. Charge Data

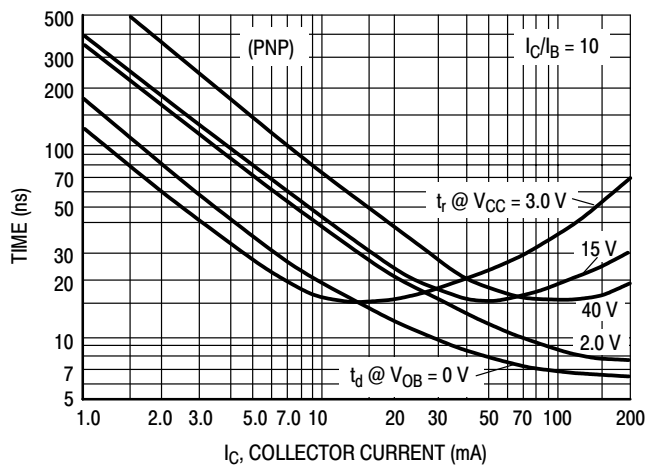


Figure 23. Turn-On Time

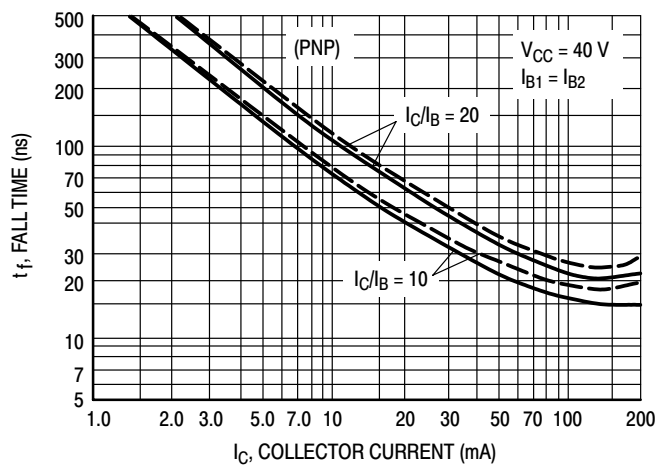


Figure 24. Fall Time

(PNP)

TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS
NOISE FIGURE VARIATIONS

($V_{CE} = -5.0$ Vdc, $T_A = 25^\circ\text{C}$, Bandwidth = 1.0 Hz)

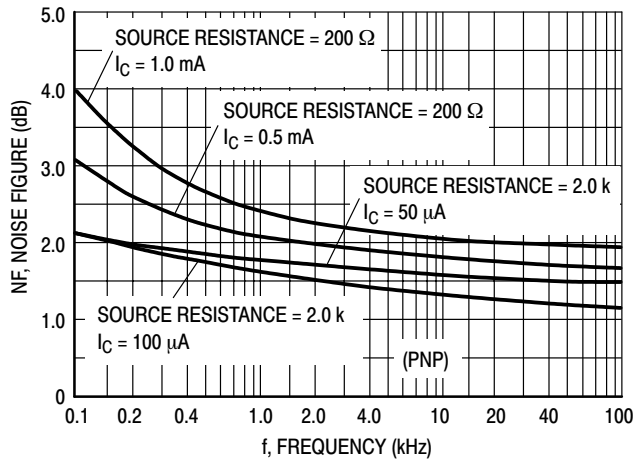


Figure 25.

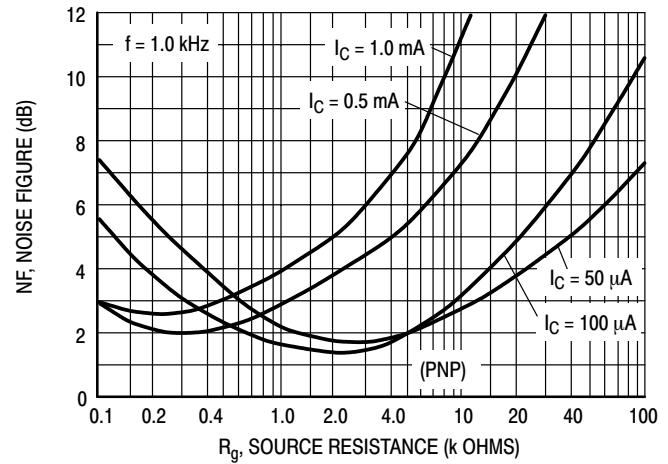


Figure 26.

h PARAMETERS

($V_{CE} = -10$ Vdc, $f = 1.0$ kHz, $T_A = 25^\circ\text{C}$)

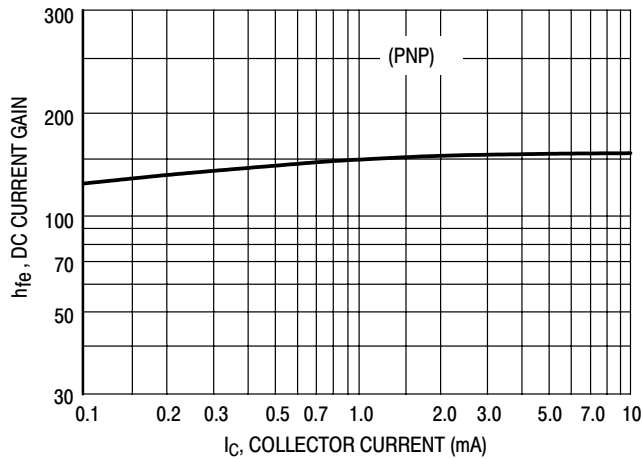


Figure 27. Current Gain

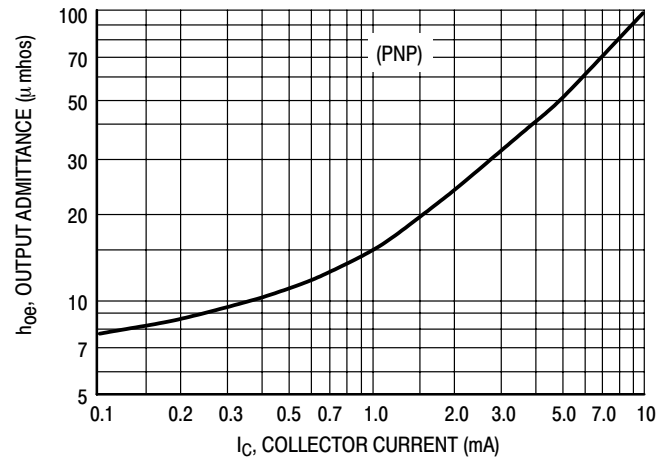


Figure 28. Output Admittance

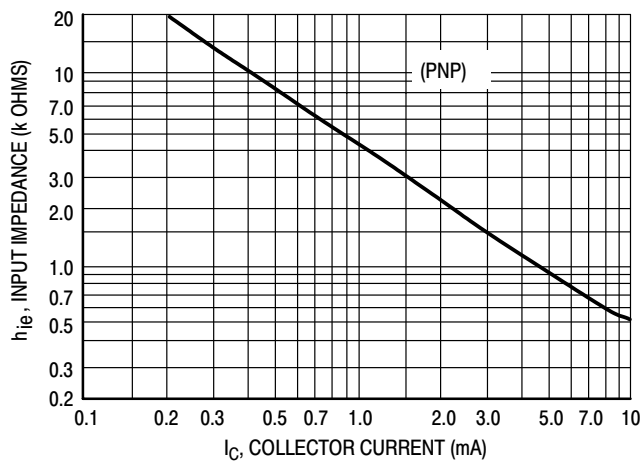


Figure 29. Input Impedance

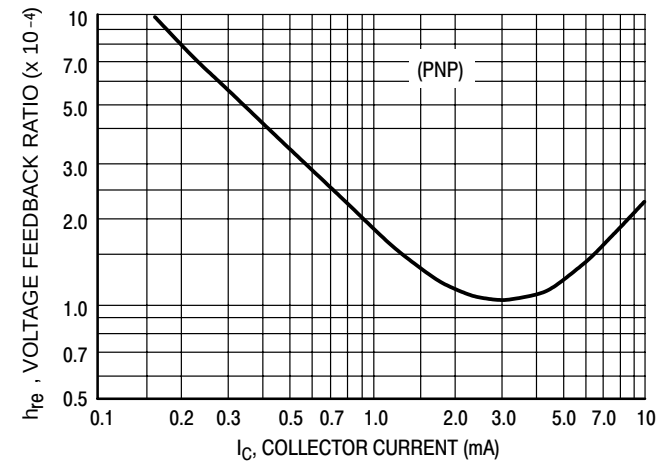


Figure 30. Voltage Feedback Ratio

MBT3946DW1T1

(PNP)

TYPICAL STATIC CHARACTERISTICS

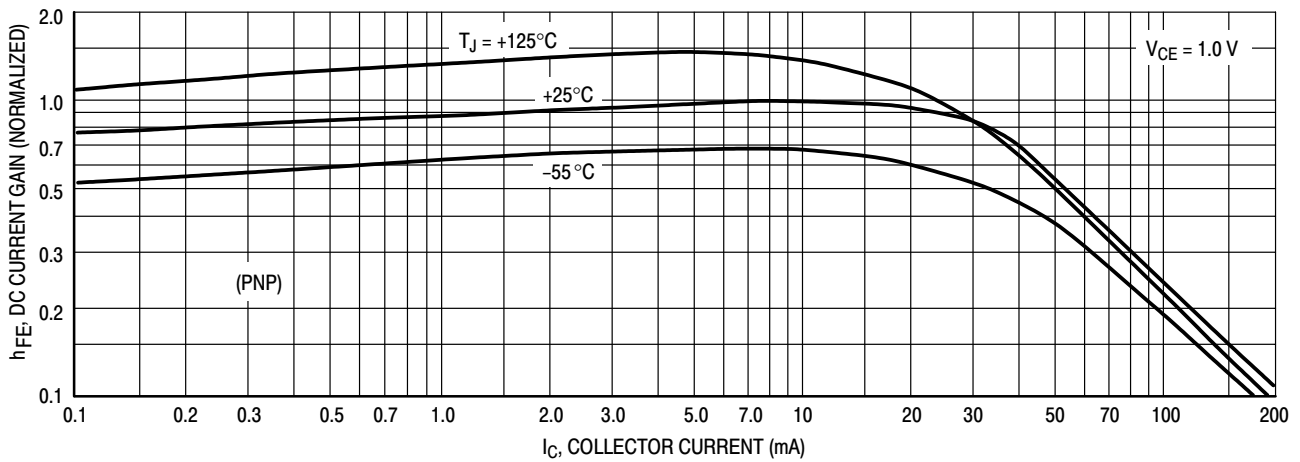


Figure 31. DC Current Gain

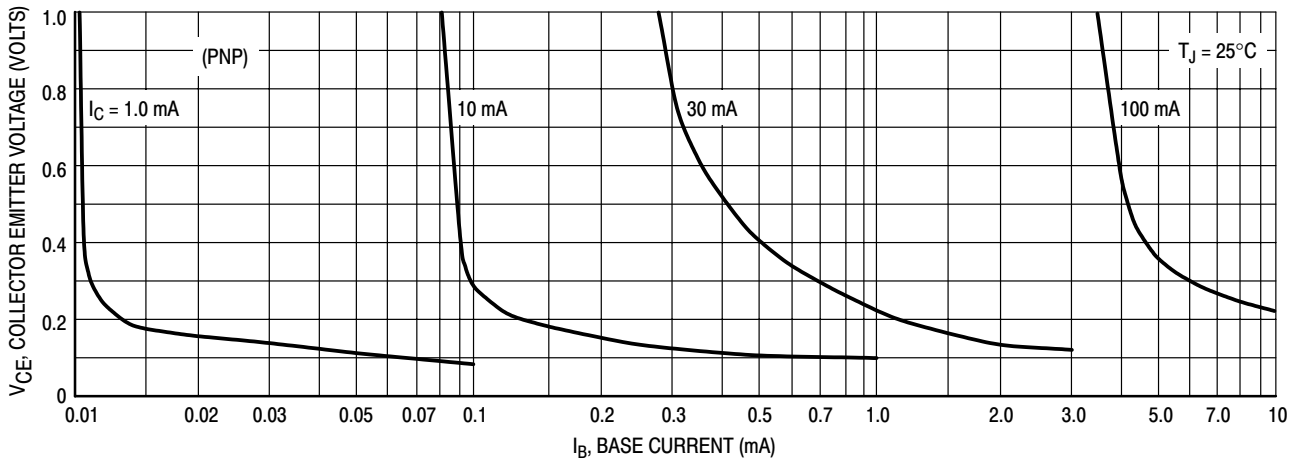


Figure 32. Collector Saturation Region

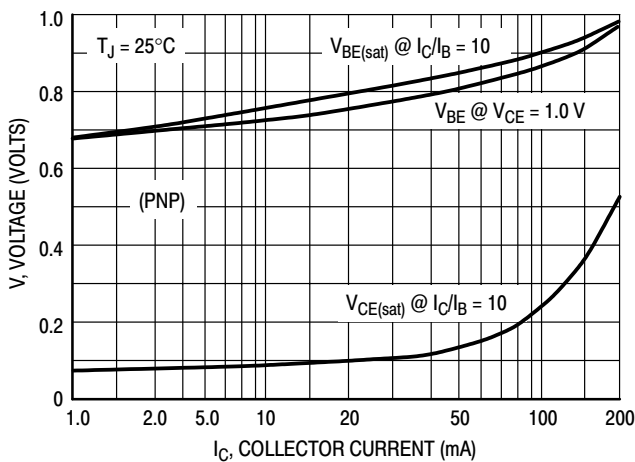


Figure 33. "ON" Voltages

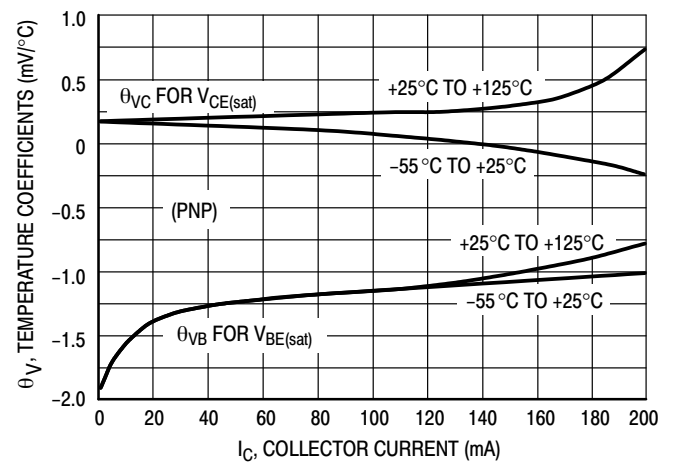
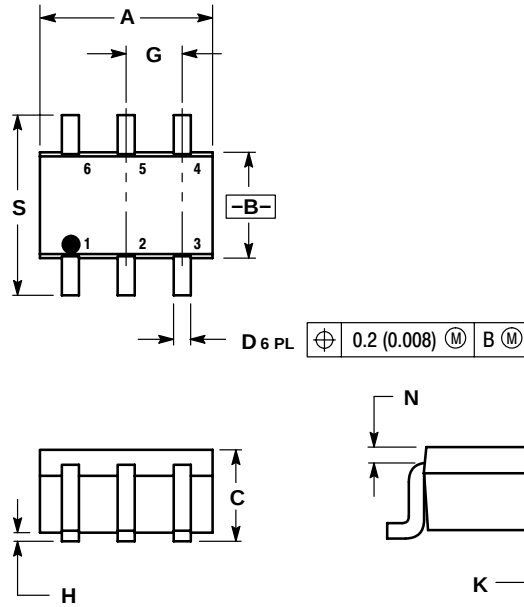


Figure 34. Temperature Coefficients

MBT3946DW1T1

PACKAGE DIMENSIONS

SOT-363-6/SC-88
CASE 419B-02
ISSUE L



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 419B-01 OBSOLETE, NEW STANDARD 419B-02.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
H	---	0.004	---	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20

STYLE 1:

- PIN 1. EMITTER 2
- BASE 2
- COLLECTOR 1
- EMITTER 1
- BASE 1
- COLLECTOR 2

SOLDERING FOOTPRINT*

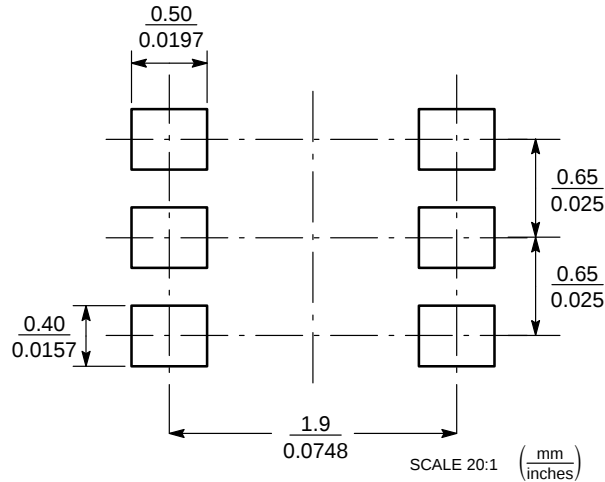


Figure 35. SC-88/SC70-6

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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